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Dhingra, Archit; Galiy, Pavlo V.; Wang, Lu; Vorobeva, Nataliia S.; Lipatov, Alexey; Torres, Angel; Nenchuk, Taras M.; Gilbert, Simeon J.; Sinitskii, Alexander; Yost, Andrew J.; Mei, Wai-Ning; Fukutani, Keisuke; Chen, Jia Shiang; and Dowben, Peter, "Corrigendum: Surface termination and Schottky-barrier formation of $\text{In}_4\text{Se}_3(001)$ [*Semiconductor Science and Technology* (2020) 35 (065009) DOI: 10.1088/1361-6641/ab7e45]" (2021). *Peter Dowben Publications*. 279.


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Corrigendum: Surface termination and Schottky-barrier formation of $\text{In}_4\text{Se}_3(001)$ (2020 *Semicond. Sci. Technol.* 35 065009)

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Received 14 April 2021

Accepted for publication 20 April 2021

Published 20 May 2021



Through the description of various surface terminations, the chain direction of In_4Se_3 in this paper [1] is implied to be in the plane of its surface. Even though the common convention for photoemission spectroscopy is to place z -axis along the surface normal, the axis perpendicular to the growth direction for this indium selenide is the crystallographic a -axis (and not the c -axis) [2–4]. Therefore, in our work the surface of In_4Se_3 should have been labeled (100), and not (001), to prevent any confusion that may have resulted from a less than conventional index notation.

Data availability statement

The data that support the findings of this study are available upon reasonable request from the authors.

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